

Description

The HM100N02 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

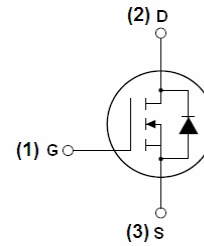
- $V_{DS} = 20V, I_D = 100A$
 $R_{DS(ON)} < 5.5m\Omega @ V_{GS} = 4.5V$
- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

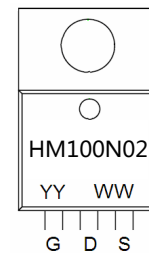
- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

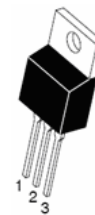
100% ΔV_{DS} TESTED!



Schematic diagram



Marking and pin Assignment



TO-220 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM100N02	HM100N02	TO-220-3L	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	100	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	70	A
Pulsed Drain Current	I_{DM}	350	A
Maximum Power Dissipation	P_D	60	W
Derating factor		0.48	W/ $^\circ C$
Single pulse avalanche energy (Note 5)	E_{AS}	200	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta JC}$	2.1	$^\circ C/W$
---	-----------------	-----	--------------

Electrical Characteristics (T_C=25°C unless otherwise noted)

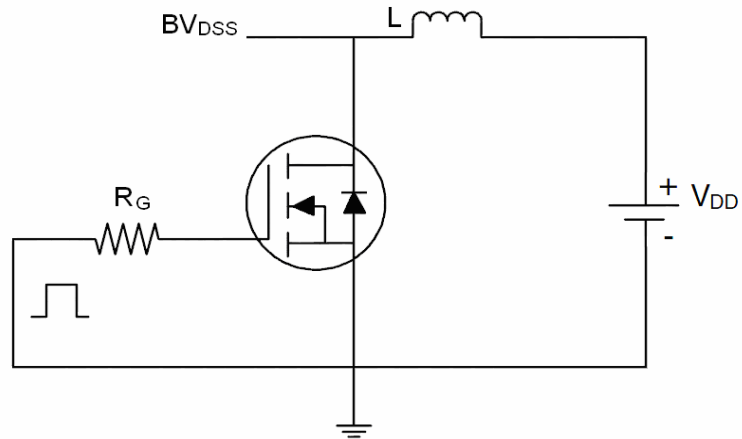
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	20	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V, V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.45	0.65	1.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =40 A	-	4.5	5.5	mΩ
		V _{GS} =4.5V, I _D =30A		6.5	7.5	mΩ
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =40A	15	-	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V, F=1.0MHz	-	2000	-	PF
Output Capacitance	C _{Oss}		-	500	-	PF
Reverse Transfer Capacitance	C _{rss}		-	200	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =10V, I _D =2A, R _L =1Ω V _{GS} =4.5V, R _G =3Ω	-	6.4	-	nS
Turn-on Rise Time	t _r		-	17.2	-	nS
Turn-Off Delay Time	t _{d(off)}		-	29.6	-	nS
Turn-Off Fall Time	t _f		-	16.8	-	nS
Total Gate Charge	Q _g	V _{DS} =10V, I _D =40A, V _{GS} =10V	-	27		nC
Gate-Source Charge	Q _{gs}		-	6.5		nC
Gate-Drain Charge	Q _{gd}		-	6.4		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =20A	-		1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	100	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 40A di/dt = 100A/μs ^(Note3)	-	25	-	nS
Reverse Recovery Charge	Q _{rr}		-	24	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

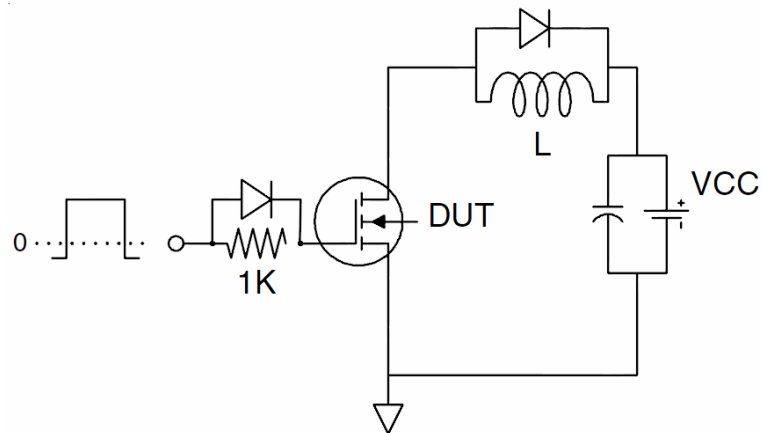
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. E_{AS} condition : T_J=25°C, V_{DD}=10V, V_G=10V, L=0.5mH, R_G=25Ω.

Test circuit

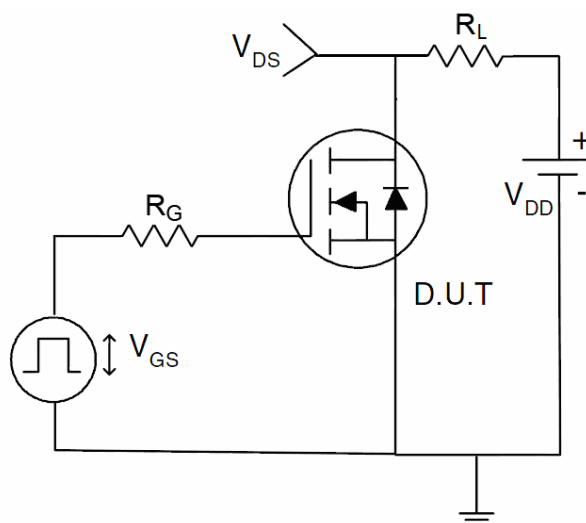
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

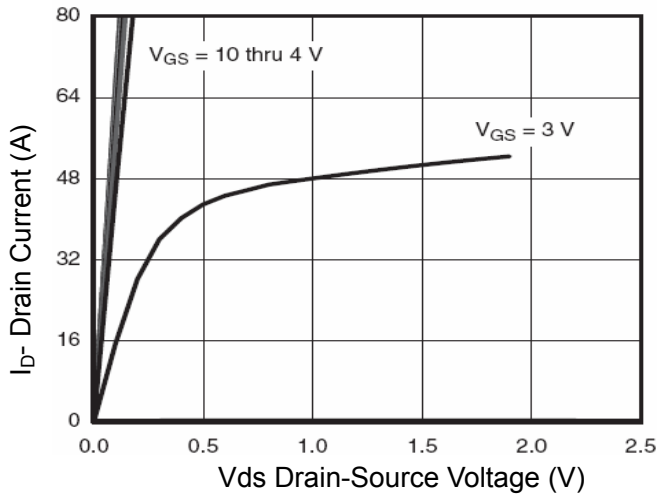


Figure 1 Output Characteristics

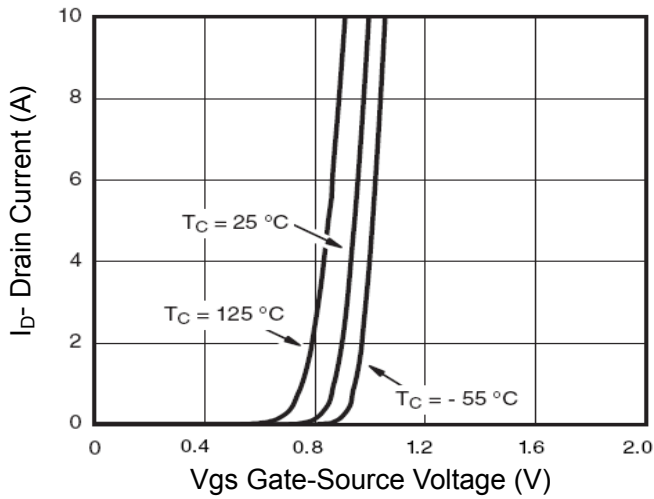


Figure 2 Transfer Characteristics

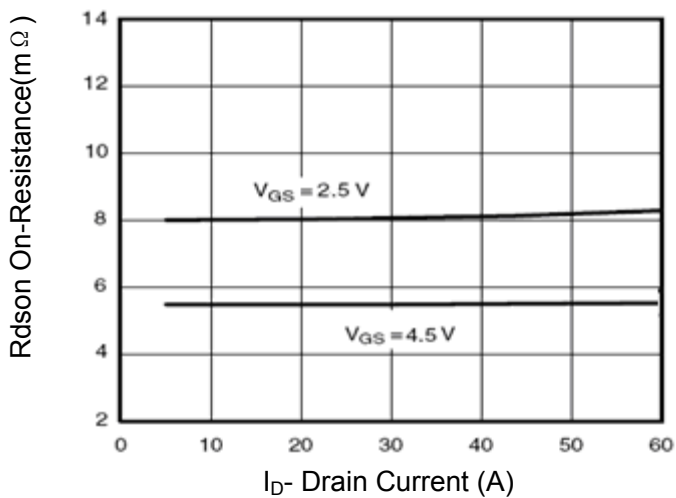


Figure 3 Rdson- Drain Current

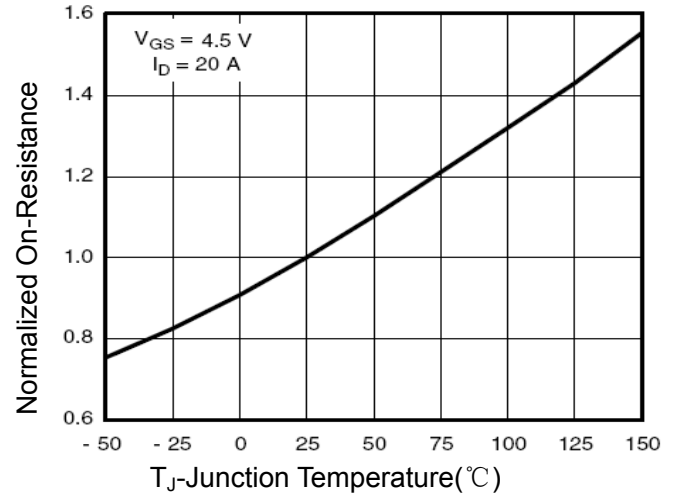


Figure 4 Rdson-Junction Temperature

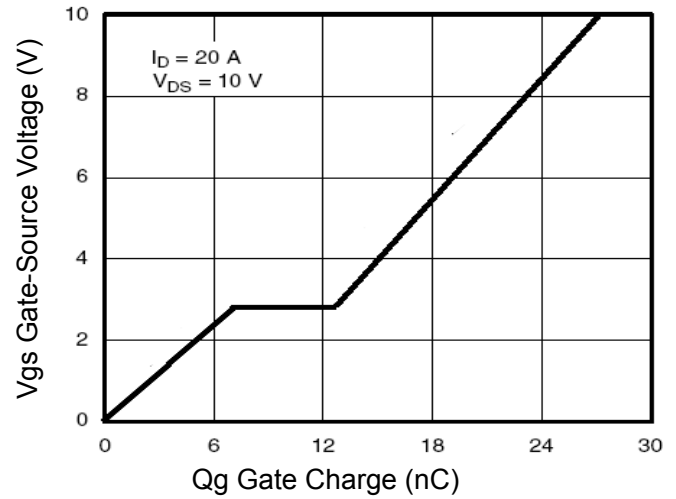


Figure 5 Gate Charge

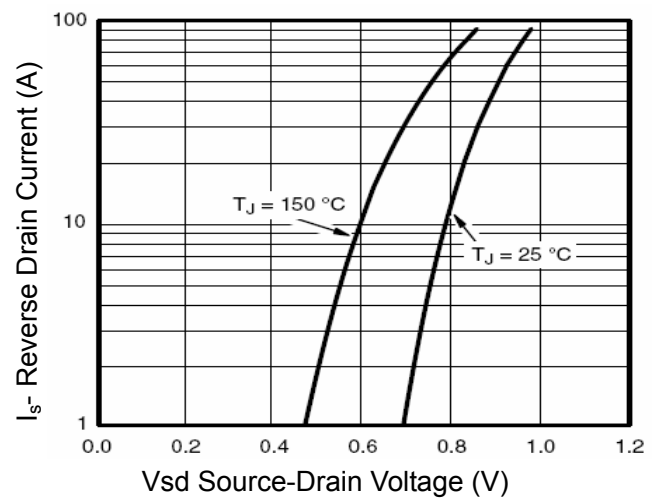


Figure 6 Source- Drain Diode Forward

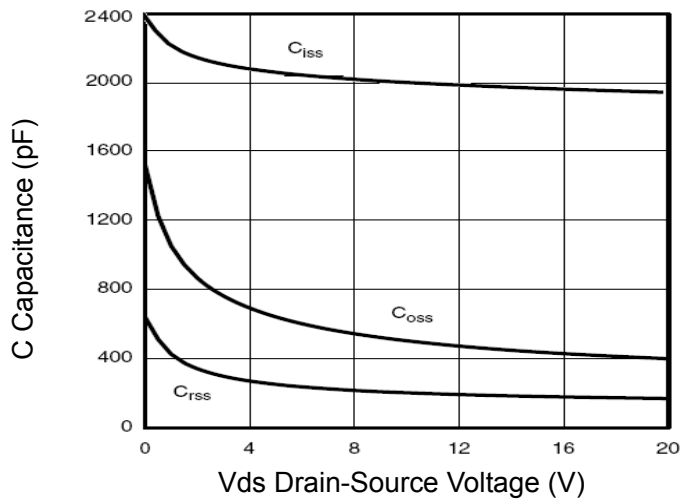


Figure 7 Capacitance vs Vds

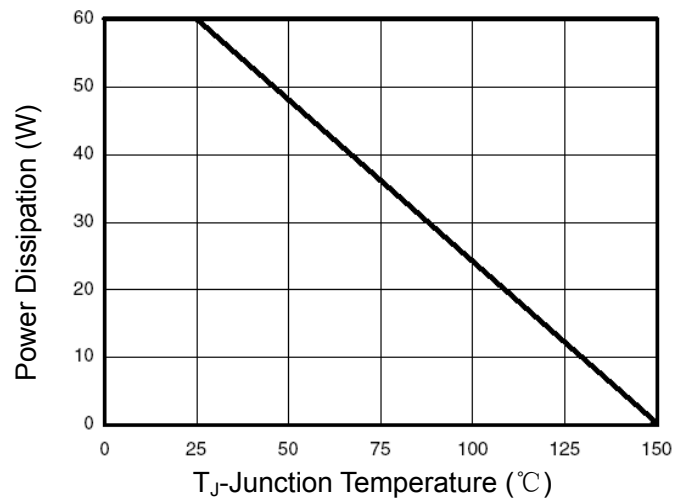


Figure 9 Power De-rating

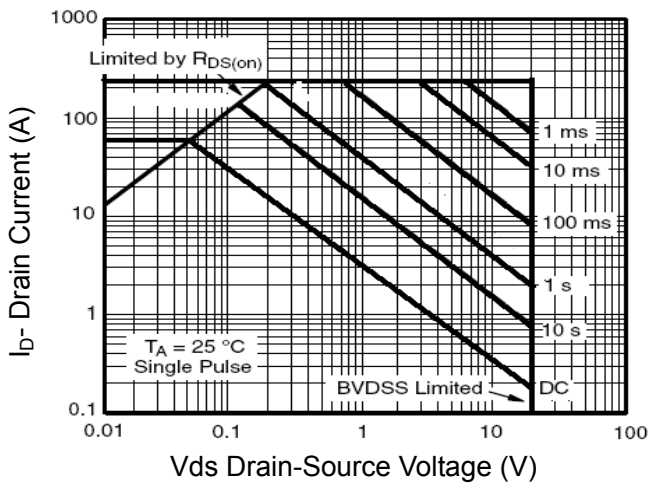


Figure 8 Safe Operation Area

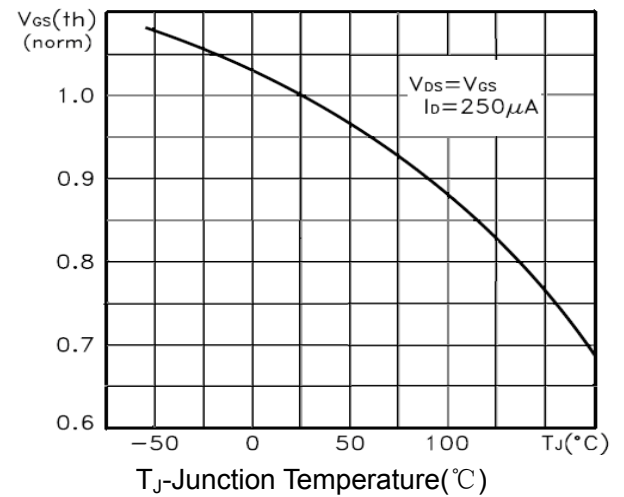


Figure 10 $V_{GS(th)}$ vs Junction Temperature

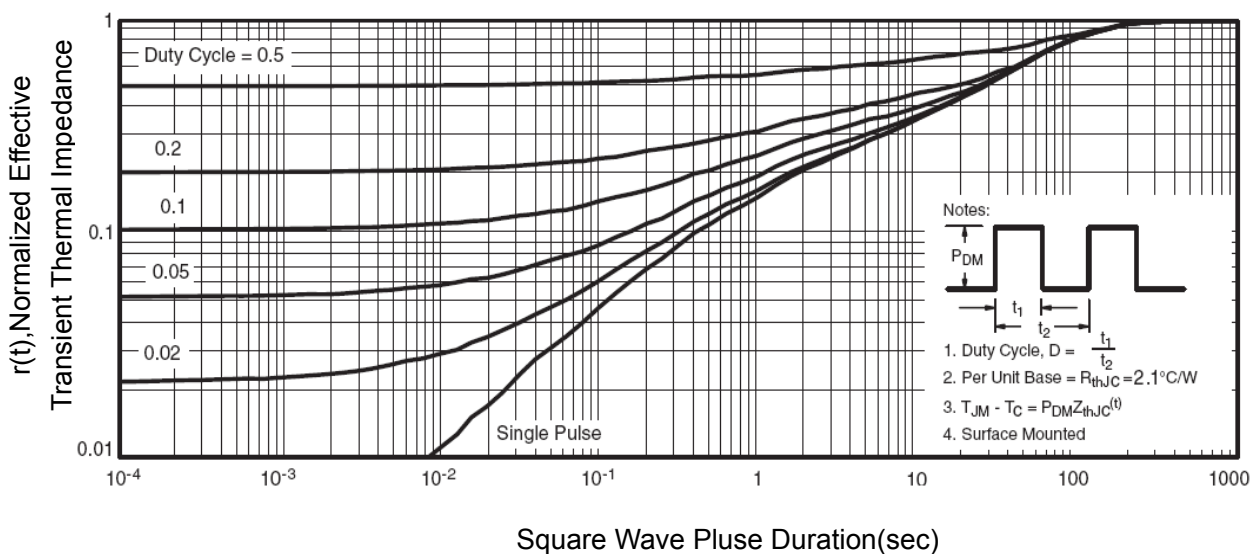
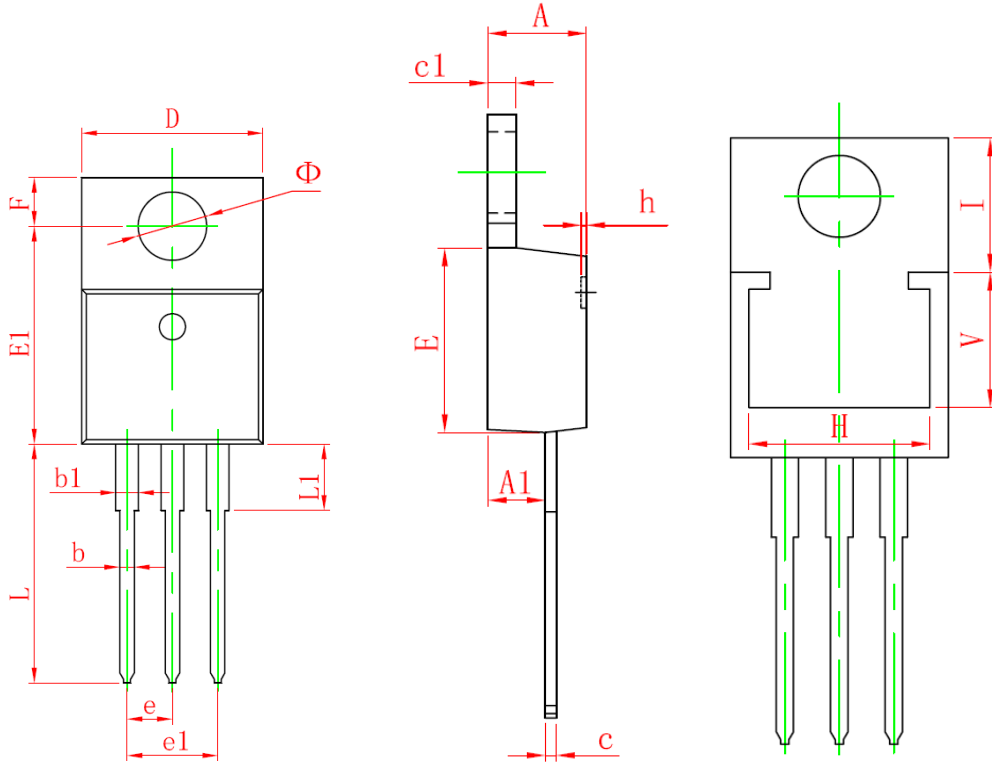


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.470	4.670	0.176	0.184
A1	2.520	2.820	0.099	0.111
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	10.010	10.350	0.394	0.407
E	8.500	8.900	0.335	0.350
E1	12.060	12.460	0.475	0.491
e	2.540 (TYP.)		0.100 (TYP.)	
e1	4.980	5.180	0.196	0.204
F	2.590	2.890	0.102	0.114
H	8.440 REF.		0.332 REF.	
h	0.000	0.300	0.000	0.012
L	13.400	13.800	0.528	0.543
L1	3.560	3.960	0.140	0.156
V	6.360 REF.		0.250 REF.	
I	6.300 REF.		0.248 REF.	
Φ	3.735	3.935	0.147	0.155